

**HIGH VOLTAGE ULTRAFAST RECTIFIER**
**MAIN PRODUCT CHARACTERISTICS**

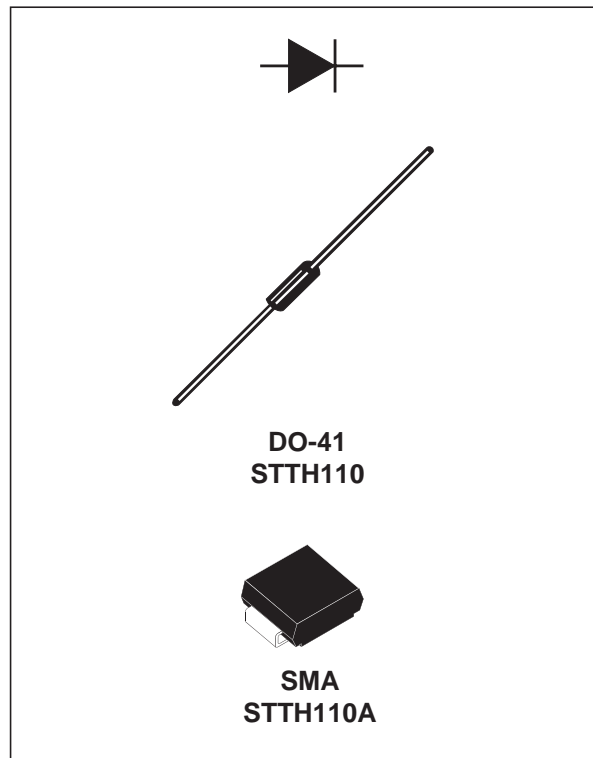
<b>I<sub>F(AV)</sub></b>	<b>1 A</b>
<b>V<sub>RRM</sub></b>	<b>1000 V</b>
<b>T<sub>j</sub> (max)</b>	<b>175 °C</b>
<b>V<sub>F</sub> (max)</b>	<b>1.42 V</b>

**FEATURES AND BENEFITS**

- Low forward voltage drop
- High reliability
- High surge current capability
- Soft switching for reduced EMI disturbances
- Planar technology

**DESCRIPTION**

The STTH110, which is using ST ultrafast high voltage planar technology, is specially suited for free-wheeling, clamping, snubbing, demagnetization in power supplies and other power switching applications.


**ABSOLUTE RATINGS (limiting values)**

Symbol	Parameter			Value	Unit
V <sub>RRM</sub>	Repetitive peak reverse voltage			1000	V
V <sub>(RMS)</sub>	RMS voltage			700	V
I <sub>F(AV)</sub>	Average forward current	TI = 100°C    δ = 0.5	DO-41	1	A
		TI = 125°C    δ = 0.5	SMA	1	
I <sub>FSM</sub>	Forward surge current    t = 8.3 ms	DO-41		20	A
		SMA		18	
T <sub>stg</sub>	Storage temperature range			- 50 + 175	°C
T <sub>j</sub>	Maximum operating junction temperature			+ 175	°C

## THERMAL PARAMETERS

Symbol	Parameter			Value	Unit
$R_{th(j-l)}$	Junction to lead	L = 10 mm	DO-41	45	°C/W
			SMA	30	
$R_{th(j-a)}$	Junction to ambient	L = 10 mm	DO-41	110	

## STATIC ELECTRICAL CHARACTERISTICS

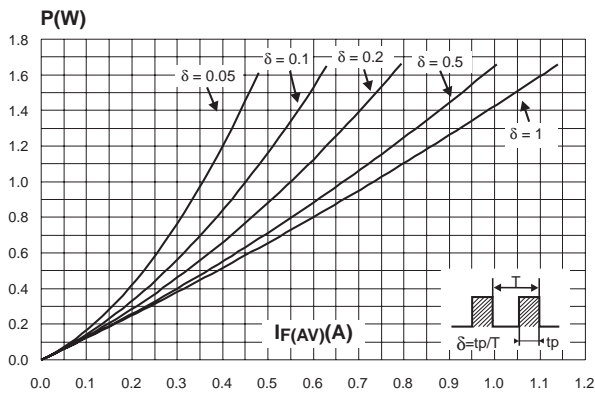
Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$I_R$	Reverse leakage current	$V_R = 1000V$	$T_j = 25^\circ C$			10	$\mu A$
			$T_j = 125^\circ C$			50	
$V_F$	Forward voltage drop	$I_F = 1 A$	$T_j = 25^\circ C$			1.7	V
			$T_j = 150^\circ C$		0.98	1.42	

To evaluate the maximum conduction losses use the following equation :  
 $P = 1.20 \times I_{F(AV)} + 0.225 \times I_{F(RMS)}^2$

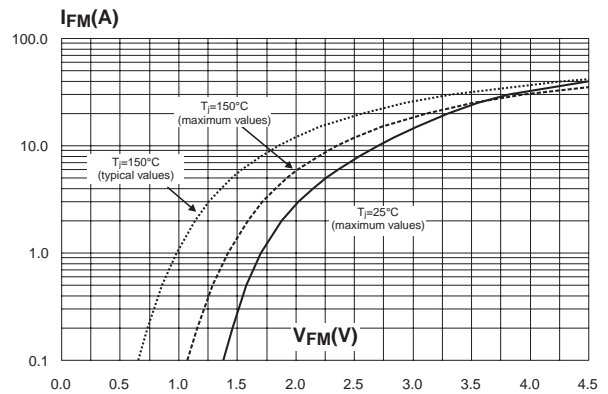
## DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$I_F = 0.5 A$ $I_{rr} = 0.25 A$ $I_R = 1A$	$T_j = 25^\circ C$			75	ns
$t_{fr}$	Forward recovery time	$I_F = 1 A$ $dI_F/dt = 50 A/\mu s$ $V_{FR} = 1.1 \times V_{Fmax}$	$T_j = 25^\circ C$			300	ns
$V_{FP}$	Forward recovery voltage						18

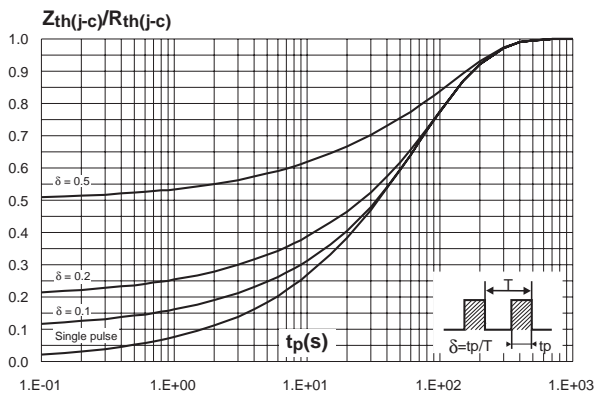
**Fig. 1:** Conduction losses versus average current.



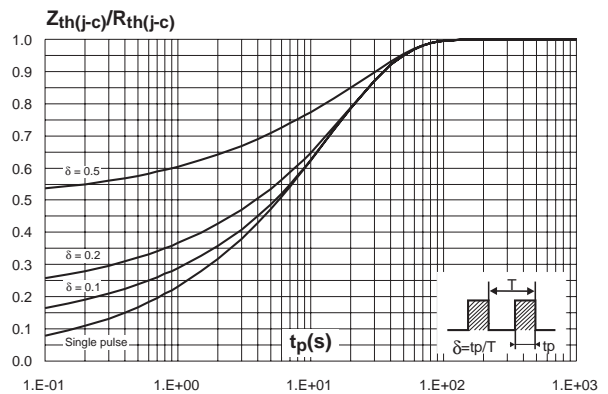
**Fig. 2:** Forward voltage drop versus forward current.



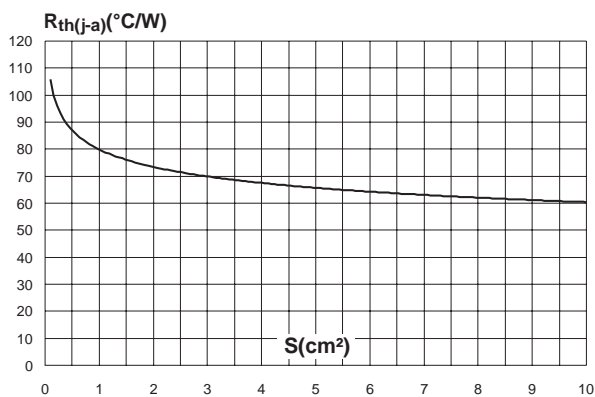
**Fig. 3-1:** Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4, L<sub>leads</sub> = 10mm) (DO-41).



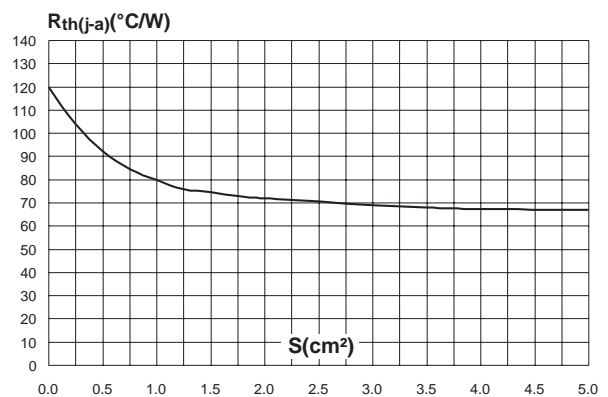
**Fig. 3-2:** Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4) (SMA).



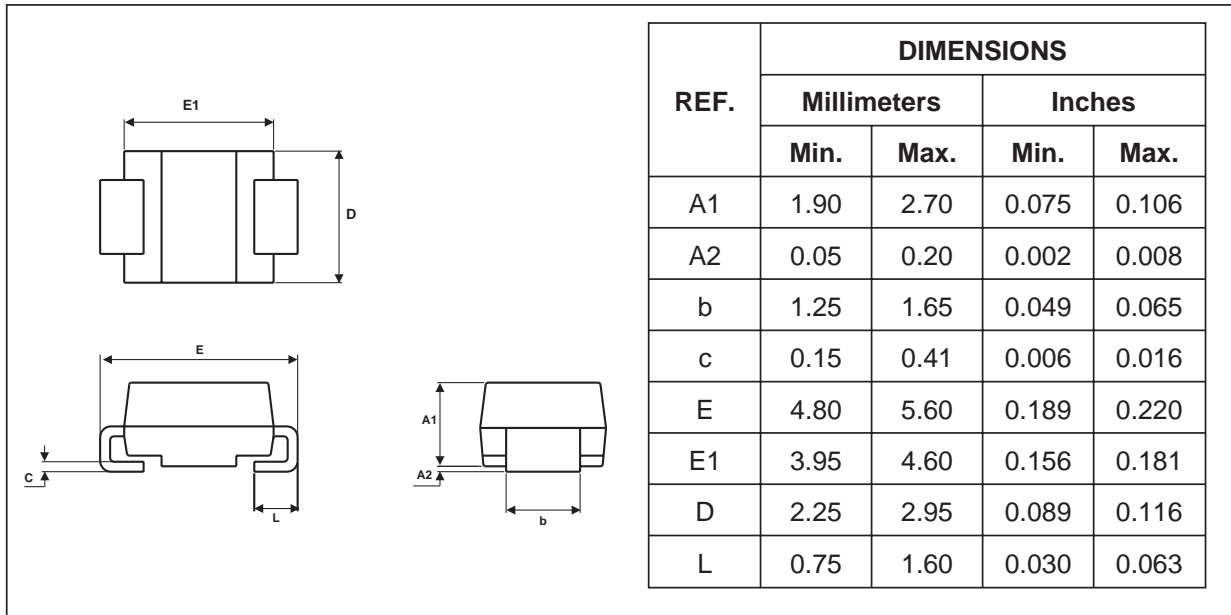
**Fig. 4-1:** Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed circuit board FR4, copper thickness: 35µm) (DO-41).



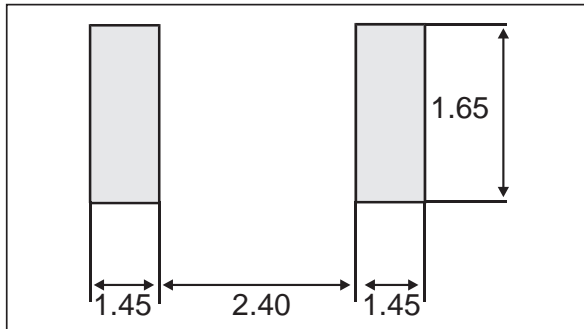
**Fig. 4-2:** Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed circuit board FR4, copper thickness: 35µm) (SMA).



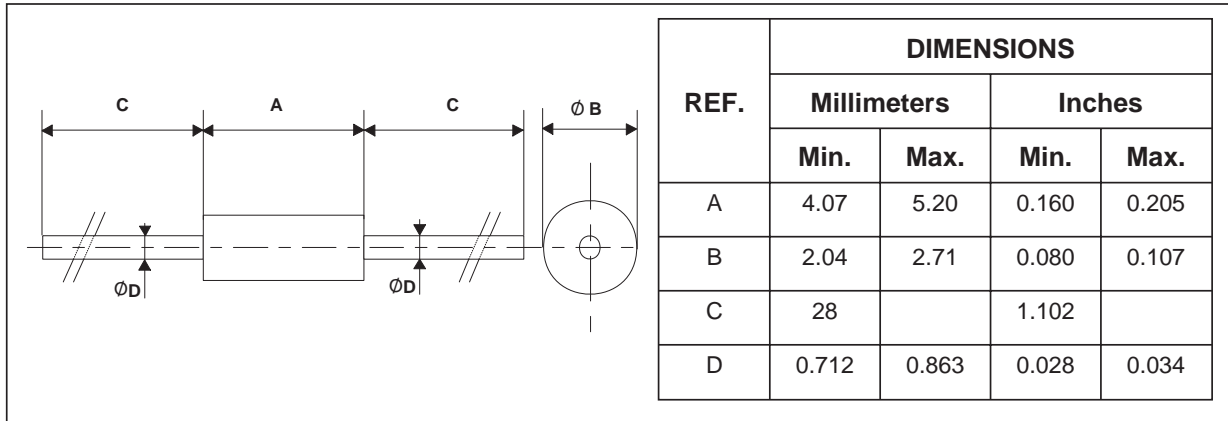
**PACKAGE MECHANICAL DATA**  
SMA



**FOOTPRINT (in millimeters)**



**PACKAGE MECHANICAL DATA**  
DO-41



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH110	STTH110	DO-41	0.34 g	2000	Ammopack
STTH110A	H10	SMA	0.068 g	5000	Tape & reel
STTH110RL	STTH110	DO-41	0.34 g	5000	Tape & reel

- Epoxy meets UL 94,V0

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